

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	3	(substrate near "process chamber") and (HCD and "hexachlorodisilane") and gas and silicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/20 13:48
S2	24	(substrate near chamber) and (HCD or "hexachlorodisilane") and gas and silicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/19 08:43
S3	14	(substrate near "process chamber") and (HCD or "hexachlorodisilane") and gas and silicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/19 08:51
S4	1	(substrate near "process chamber") and (HCD or "hexachlorodisilane") and gas and silicon and hydrogen and germanium and phosphor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/19 08:53
S6	4	(substrate near "process chamber") and (HCD or "hexachlorodisilane") and gas and silicon and hydrogen and germanium	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/19 08:53
S7	11	(substrate near "process chamber") and (HCD or "hexachlorodisilane") and gas and silicon and hydrogen	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/25 15:08
S8	114840	(substrate or semiconductor or wafer) near8 chamber	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 11:14
S9	16269	((anneal\$4 or heat\$4) near4 (substrate or semiconductor or wafer)) near8 chamber	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 11:15

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S10	21	((anneal\$4 or heat\$4) near4 (substrate or semiconductor or wafer)) near8 chamber and "HCD"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 11:15
S11	6	((anneal\$4 or heat\$4) near4 (substrate or semiconductor or wafer)) near8 chamber and ("HCD" near4 chamber)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 11:16
S12	6	((anneal\$4 or heat\$4) near4 (substrate or semiconductor or wafer)) near8 chamber and ("HCD" near4 chamber) and (("SiGe" or "silicon germanium" or silicon or "Si") near4 film)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/23 11:17
S13	12	((substrate or semiconductor or wafer) near8 chamber) and (heat or thermal) and ("HCD" or "hexachlorodisilane") and (silicon near4 epitaxial)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/20 13:51
S14	16	((substrate or carrier or base or wafer) near9 chamber) and (heat\$4 or anneal\$4 or thermal) and (("HCD" or hexachlorodisilane) near9 gas) and (silicon near9 epitaxial)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/07 07:39
S15	16	((substrate or carrier or base or wafer) near9 chamber) and (heat\$4 or anneal\$4 or thermal) and (("HCD" or hexachlorodisilane) near9 gas) and (silicon near9 epitaxial)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/07 07:36
S16	12	((substrate or carrier or base or wafer) near9 chamber) and (heat\$4 or anneal\$4 or thermal) and (("HCD" or hexachlorodisilane) near9 gas) and (silicon near9 epitaxial) and (SiGe or (silicon near germanium))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/07 07:37

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S17	5	((substrate or carrier or base or wafer) near9 chamber) and (heat\$4 or anneal\$4 or thermal) and ("HCD" or hexachlorodisilane) near9 gas) and (silicon near9 epitaxial) and (SiGe or (silicon near germanium)) and (crystalline near4 silicon)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/07 07:37
S18	12	((substrate or carrier or base or wafer) near9 chamber) and (heat\$4 or anneal\$4 or thermal) and ("HCD" or hexachlorodisilane) near9 gas) and (silicon near9 epitaxial) and (SiGe or (silicon near germanium)) and silicon	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/07 07:38
S19	16	(substrate or carrier or base or wafer) and chamber and (heat\$4 or anneal\$4 or thermal) and ("HCD" or hexachlorodisilane) near9 gas) and (silicon near9 epitaxial)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/07 07:40
S20	45	(substrate or carrier or base or wafer) and (chamber or vacuum) and (heat\$4 or anneal\$4 or thermal) and ("HCD" or hexachlorodisilane) and gas and (silicon near9 epitaxial)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/07 07:40
S21	34	(substrate or carrier or base or wafer) and (chamber or vacuum) and (heat\$4 or anneal\$4 or thermal) and ("HCD" or hexachlorodisilane) and gas and (silicon near9 epitaxial) and (SiGe or (silicon near germanium))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/07 07:42